IN THE CLAIMS

This listing of claims replaces all prior versions and listings of the claims in the above-referenced application.

1. (Canceled).

2. (Previously Presented) The method of claim 3 wherein said semiconductor light emitter has at least one light extraction surface from where light is intended to be extracted, and wherein said forming is done on at least one extraction surface of said semiconductor light emitter.

3. (Currently Amended) A method of forming a light emitting device, said method comprising:

forming at least one of Fresnel lens and holographic diffuser on at least one surface of a semiconductor light emitter to affect light emitted by said semiconductor light emitter;

wherein ~~said forming comprises pressing a stamping block against at least one surface of said semiconductor light emitter, the stamping block comprising a material selected from the group of molybdenum, titanium, zirconium, graphite, silicon carbide, sapphire, stainless steel, tungsten, tantalum, columbium, and alloys thereof~~ the at least one surface is one of an alloy comprising $(Al_xGa_{1-x})_yIn_{1-y}P$ where $0 \leq x \leq 1$ and $0 \leq y \leq 1$ and a III-nitride alloy.

4. (Previously Presented) The method of claim 3 wherein said forming is executed concurrently with a wafer-bonding process, said wafer-bonding process comprising:

removing a first substrate of said semiconductor light emitter; and

bonding a second substrate to said semiconductor light emitter.

5. (Currently Amended) A method of forming a light emitting device, said method comprising:

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forming at least one of Fresnel lens and holographic diffuser on at least one surface of a semiconductor light emitter to affect light emitted by said semiconductor light emitter;

wherein said forming comprises at least one method selected from ablation, machining, scribing, and electron discharge machining; and

wherein the at least one surface is one of an alloy comprising $(Al_xGa_{1-x})_yIn_{1-y}P$ where $0 \leq x \leq 1$ and $0 \leq y \leq 1$ and a III-nitride alloy.

6. (Withdrawn) The method of claim 1 further comprising:

beveling one or more sides of said semiconductor light emitter.

7. (Previously Presented) The method of claim 3 wherein said semiconductor light emitter has a light emitting layer, the method further comprising:

confining light emission to a preselected section of said light emitting layer.

8. (Previously Presented) The method of claim 3 wherein said semiconductor light emitter has a light emitting layer, the method further comprising confining light emission to a preselected section of said light emitting layer, wherein said confining comprises at least one method selected from applying the Holonyak process, using selective area growth, using selective area bonding, using diffusion, and using ion implantation.

9. (Previously Presented) The method of claim 3 further comprising:

coating one or more surfaces of said semiconductor light emitter with a reflective material.

10. (Previously Presented) The method of claim 3 further comprising:

coating said Fresnel lens or said holographic diffuser with a reflective material.

11. (Original) The method of claim 2 further comprising:

forming an optical element on the surface opposite of said extraction surface.

12. (Previously Presented) A light emitting device comprising:

a semiconductor light emitter; and

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a first optical element stamped on at least one surface of said semiconductor light emitter, said first optical element comprising one of Fresnel lens and holographic diffuser;

wherein the stamped surface is one of an alloy comprising $(Al_xGa_{1-x})_yIn_{1-y}P$ where $0 \leq x \leq 1$ and $0 \leq y \leq 1$ and a III-nitride alloy.

13. (Original) The device of claim 12 further comprising:

a reflective material coating at least one surface of said device.

14. (Withdrawn) The device of claim 12 wherein a light emitting layer of said semiconductor light emitter is made to emit photons primarily towards a preselected section of said first optical element.

15. (Withdrawn) The device of claim 12 wherein at least one surface of light emitting device is beveled.

16. (Withdrawn) The device of claim 12 wherein said semiconductor light emitter is a confined-emission spot light emitting diode.

17. (Withdrawn) The device of claim 12 wherein said semiconductor light emitter and said first optical element comprise $(Al_xGa_{1-x})_yIn_{1-y}P$ where $0 \leq x \leq 1$ and $0 \leq y \leq 1$.

18. (Withdrawn) The device of claim 12 wherein said light-emitting diode comprises a III-nitride semiconductor alloy and said first optical element comprises one of silicon carbide and sapphire.

19. (Withdrawn) The device of claim 12 wherein said semiconductor light emitter and said first optical element comprise aluminum gallium arsenide semiconductor alloy.

20. (Withdrawn) The device of claim 12, wherein said semiconductor light emitter has a flip-chip configuration.

21. (Withdrawn) The device of claim 12, wherein said semiconductor light emitter has a configuration in which a light emitting layer of said semiconductor light

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emitter is substantially perpendicular to said Fresnel lens.

22. (Withdrawn) The device of claim 12, wherein the radiation pattern of said device is controlled by the ratio of the focal length of said first optical element to the distance between said first optical element and a light-emitting layer of said semiconductor light emitter.

23. (Original) The device of claim 12, wherein said first optical element is designed to achieve one of light focusing, light collimating, and light diverging.

24. (Original) The device of claim 12 wherein said first optical element is designed to direct light in a preselected direction.

25. (Withdrawn) The device of claim 12 further comprising:

a second optical element on a surface of said semiconductor light emitter opposite the surface having said first optical element.

26. (Withdrawn) The device of claim 25 wherein at least one of said first Fresnel lens and said second Fresnel lens is designed to focus light.

27. (Currently Amended) A method of forming a light emitting device, said method comprising:

stamping at least one optical element on at least one surface of a semiconductor light emitter to affect the light emitted by said semiconductor light emitter ~~using a stamping block comprising a material selected from the group of molybdenum, titanium, zirconium, graphite, silicon carbide, sapphire, stainless steel, tungsten, tantalum, columbium, and alloys thereof~~

wherein the stamped surface is one of an alloy comprising $(Al_xGa_{1-x})_yIn_{1-y}P$ where $0 \leq x \leq 1$ and $0 \leq y \leq 1$ and a III-nitride alloy.

28. (Original) The method of claim 27 further comprising:

coating a surface of said light emitting device with a reflective layer.

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29. (Original) The method of claim 27 wherein said stamping is done on at least one of a semiconductor layer and a substrate layer of said semiconductor light emitter.

30. (Original) The method of claim 29 wherein said semiconductor layer comprises a transparent aluminum-bearing compound.

31. (Original) The method of claim 27, wherein said stamping is executed at an elevated temperature, said elevated temperature being higher than room temperature.

32. (Original) The method of claim 31, further comprising lowering said elevated temperature to facilitate the separation of a stamping block from said semiconductor light emitter after said stamping.

33. (Original) The method of claim 32, wherein said elevated temperature is higher than the ductile transition temperature of the material constituting said at least one surface on which said optical element is formed.

34. (Previously Presented) A light emitting device comprising:

a semiconductor light emitter; and

at least one optical element stamped on at least one surface of said semiconductor light emitter, wherein said optical element is a first optical element;

wherein the stamped surface is one of an alloy comprising $(Al_xGa_{1-x})_yIn_{1-y}P$ where $0 \leq x \leq 1$ and $0 \leq y \leq 1$ and a III-nitride alloy.

35. (Withdrawn) The device of claim 34 wherein a light emitting layer of said semiconductor light emitter is made to emit photons primarily toward a preselected section of said first optical element.

36. (Withdrawn) The device of claim 34 wherein said light-emitting and said first optical element comprise $(Al_xGa_{1-x})_yIn_{1-y}P$ where $0 \leq x \leq 1$ and $0 \leq y \leq 1$.

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37. (Withdrawn) The device of claim 34 wherein said semiconductor light emitter comprises a III-nitride semiconductor alloy and said first optical element comprises one of silicon carbide and sapphire.

38. (Withdrawn) The device of claim 34 wherein said semiconductor light emitter and said first optical element comprise aluminum gallium arsenide semiconductor alloy.

39. (Withdrawn) The device of claim 34 wherein said light emitting diode has a flip-chip configuration.

40. (Withdrawn) The device of claim 34 wherein said light emitting diode has a configuration in which the light emitting layer of said light emitting diode is substantially perpendicular to said Fresnel lens.

41. (Previously Presented) A light emitting diode array comprising a plurality of light emitting devices, a light emitting device comprising:

a semiconductor light emitter; and

one of a Fresnel lens and a holographic diffuser stamped on a surface of said semiconductor light emitter;

wherein the stamped surface is one of an alloy comprising $(Al_xGa_{1-x})_yIn_{1-y}P$ where $0 \leq x \leq 1$ and $0 \leq y \leq 1$ and a III-nitride alloy.

42. (Previously Presented) A light emitting array comprising a plurality of light emitting devices, a light emitting device comprising:

a semiconductor light emitter; and

an optical element stamped on a surface of said semiconductor light emitter;

wherein the stamped surface is one of an alloy comprising $(Al_xGa_{1-x})_yIn_{1-y}P$ where $0 \leq x \leq 1$ and $0 \leq y \leq 1$ and a III-nitride alloy.

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43. (Previously Presented) A display device comprising at least one blue light emitting device, at least one green light emitting device, and at least one red light emitting device, wherein at least one of said blue light emitting device, green light emitting device, and red light emitting device comprises:

a semiconductor light emitter; and

one of a Fresnel lens and a holographic diffuser stamped on a surface of said semiconductor light emitter;

wherein the stamped surface is one of an alloy comprising $(Al_xGa_{1-x})_yIn_{1-y}P$ where $0 \leq x \leq 1$ and $0 \leq y \leq 1$ and a III-nitride alloy.

44. (Previously Presented) A display device comprising at least one blue light emitting device, at least one green light emitting device, and at least one red light emitting device, wherein at least one of said blue light emitting device, green light emitting device, and red light emitting device comprises:

a semiconductor light emitter; and

one optical element stamped on a surface of said semiconductor light emitter;

wherein the stamped surface is one of an alloy comprising $(Al_xGa_{1-x})_yIn_{1-y}P$ where $0 \leq x \leq 1$ and $0 \leq y \leq 1$ and a III-nitride alloy.

45. (Currently Amended) A method for forming a light emitting device, said method comprising:

stamping an optical element in a material, said material being transparent to light emitted from said light emitting device, said material being one of high index optical glass, III-V semiconductors, II-VI semiconductors, group IV semiconductors, high-index organic semiconductors, high index organic compounds, and mixtures or alloys thereof; and

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bonding said material to a semiconductor light emitter, the bond being formed at an interface between the material and a surface of the semiconductor light emitter from which light exits the emitter.

46. (Previously Presented) The method of Claim 45, wherein said stamping precedes said bonding.

47. (Previously Presented) The method of Claim 45, wherein said bonding precedes said stamping.

48. (Withdrawn) The device of Claim 18, wherein said semiconductor light emitter has a flip-chip configuration.

49. (Withdrawn) The device of Claim 37, wherein said semiconductor light emitter has a flip-chip configuration.

50. (Previously Presented) The method of Claim 45, wherein bonding comprises bonding said material to a semiconductor light emitter with a bonding material, said bonding material being one of high index optical glass, III-V semiconductors, II-VI semiconductors, group IV semiconductors, high-index organic semiconductors, high index organic compounds, and mixtures or alloys thereof.

51. (Previously Presented) The method of Claim 45, wherein bonding comprises pressing said material together with said semiconductor light emitter at a temperature greater than room temperature.

52. (Currently Amended) A light emitting device comprising:

a semiconductor light emitter; and

an optical element stamped on a material transparent to light emitted from said light emitting device, said material being one of high index optical glass, III-V semiconductors, II-VI semiconductors, group IV semiconductors, high-index organic semiconductors, high index organic compounds, and mixtures or alloys thereof;

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wherein said material is bonded to said semiconductor light emitter, the bond being formed at an interface between the material and a surface of the semiconductor light emitter from which light exits the emitter.

53. (New) The method of claim 3 wherein said forming comprises pressing a stamping block against at least one surface of said semiconductor light emitter, the stamping block comprising a material selected from the group of molybdenum, titanium, zirconium, graphite, silicon carbide, sapphire, stainless steel, tungsten, tantalum, columbium, and alloys thereof.

54. (New) The method of claim 27 wherein stamping comprises using a stamping block comprising a material selected from the group of molybdenum, titanium, zirconium, graphite, silicon carbide, sapphire, stainless steel, tungsten, tantalum, columbium, and alloys thereof.

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